

• General Description

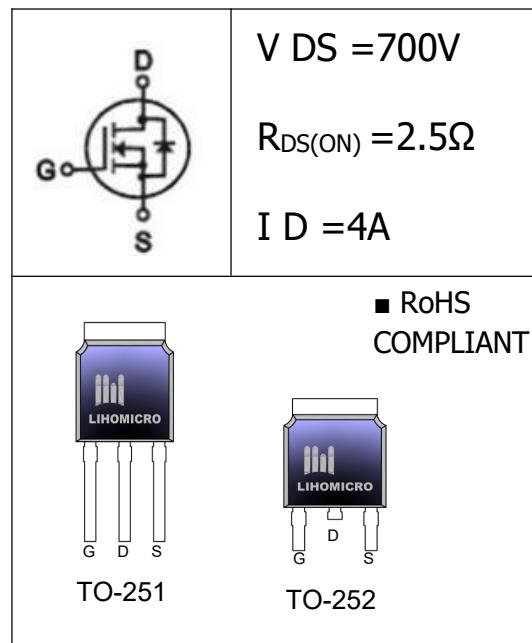
The LH4N70F combines advanced trench MOSFET technology with a low resistance package to provide extremely low RDS(ON) . This device is ideal for load switch and battery protection applications

• Features

- Low ON-resistance
- fast switching
- high input resistance
- RoHS compliant

• Application

- electronic ballast
- electronic transformer
- switch mode power supply


• Ordering Information:

Part number	LH4N70F	LH4N70F
Package	TO-252	TO-251
Basic ordering unit (pcs)	1000	1000
Normal Package Material Ordering Code	LH4N70T5-TO252-TAP	LH4N70T1-TO251-TU
Halogen Free Ordering Code	LH4N70T5-TO252-TAP-HF	LH4N70T1-TO251-TU-HF

• Absolute Maximum Ratings (T_c =25°C)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V _{DS}	700	V
Gate-Source Voltage	V _{GS}	±30	V
Continuous Drain Current(TC=25°C)	I _D	4.0	A
Continuous Drain Current TC=100°C	I _D	2.5	A
Pulsed Drain Current ¹	I _{DM}	16	A
Total Power Dissipation(TC=25°C)	P _{tot}	50	W
Operating Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55- 150	°C
Single Pulse Avalanche Energy ²	E _{AS}	260	mJ

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	700			V
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_j$	$I_D=250\mu A$, Referenced to $25^\circ C$		0.6		$V/^{\circ}C$
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	2.0		4.0	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=600V, V_{GS}=0V, T_j=25^\circ C$			25	μA
		$V_{DS}=480V, V_{GS}=0V, T_j=125^\circ C$			250	
Gate- Source Leakage Current	I_{GSS}	$V_{GS}=\pm 30V$			± 100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=2.0A$		2.5	2.8	Ω
Forward Transconductance ³	g_{FS}	$V_{DS}=40V, I_D=2.0A$		2.5		S
Reverse Diode dv/dt	dv/dt	$ISD \leq 4A, T_j=25^\circ C$		5.5		V/ns

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	$V_{GS}=0V, V_{DS}=25V$ $F=1.0MHz$		590	650	pF
Output capacitance	C_{oss}			48	55	
Reverse transfer capacitance	C_{rss}			5	12	
Turn -Off Delay Time	$T_{d(off)}$	$V_{DD}=300V, I_D=4.0A$ $R_G=25\Omega$		20		ns
Total Gate Charge	Q_g	$I_D=4.0A, V_{DS}=520V$ $V_{GS}=10V$		14.3		nC
Gate-to-Source Charge	Q_{gs}			2.8		
Gate-to-Drain Charge	Q_{gd}			4.6		
Continuous Diode Forward Current	I_s				4.0	A
Diode Forward Voltage	V_{SD}	$T_j=25^\circ C, I_s=4.0A$ $V_{GS}=0V$			1.4	V
Reverse Recovery Time	trr	$T_j=25^\circ C, I_f=4.0A$ $di/dt=100A/\mu s$		390		ns
Reverse Recovery Charge	Q_{rr}			1.5		uC

•Thermal resistance

Parameter	Symbol	Typ.	Max.	Unit
Thermal resistance, junction - case	R _{thJC}		3.47	°C/W
Thermal resistance, junction - ambient	R _{thJA}		110	°C/W

Notes:

- 1.Repetitive rating: Pulse width limited by maximum junction temperature
- 2.Starting T_j=25°C, V_{DD}=50V, L=10mH, R_G=25Ω, I_{AS}=4.0A
- 3.Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%

- Typical Characteristics

Fig1 Typical Output Characteristics, $T_c=25^\circ\text{C}$

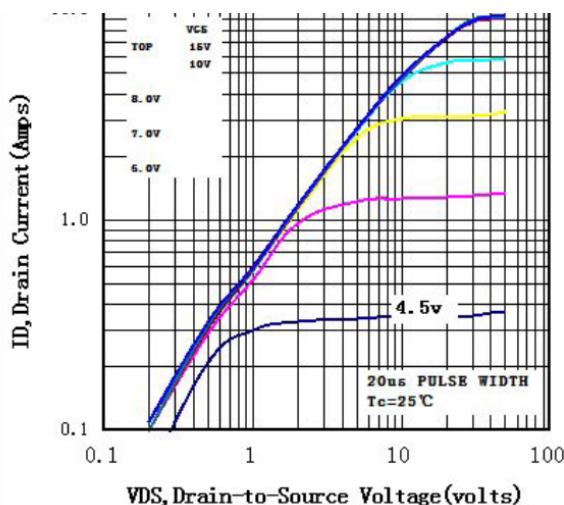


Fig2 Typical Output Characteristics, $T_c=150^\circ\text{C}$

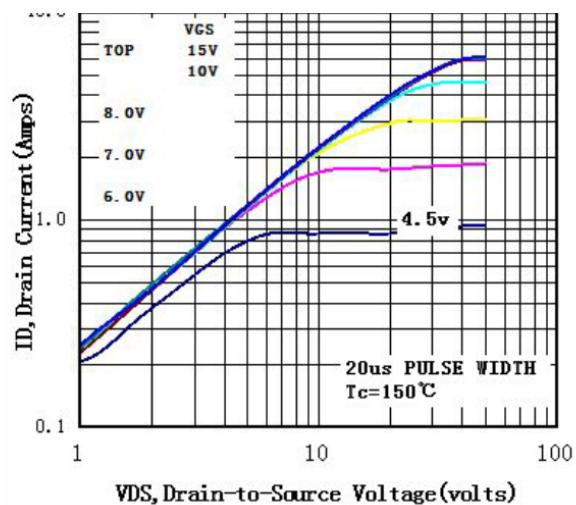


Fig3 Normalized Resistance Vs.Temperature

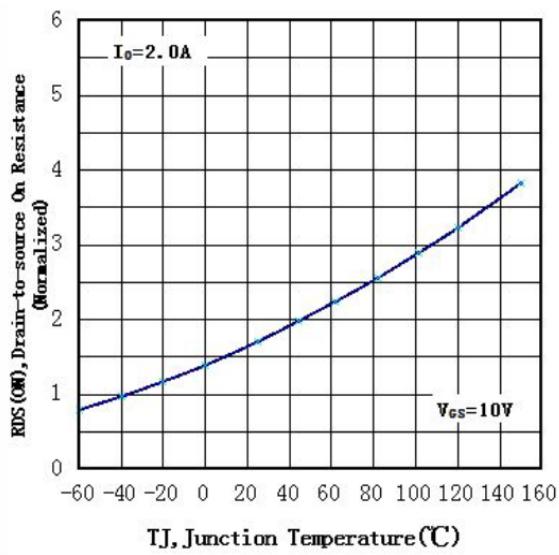


Fig4 Typical Source-Drain Diode Forward Voltage

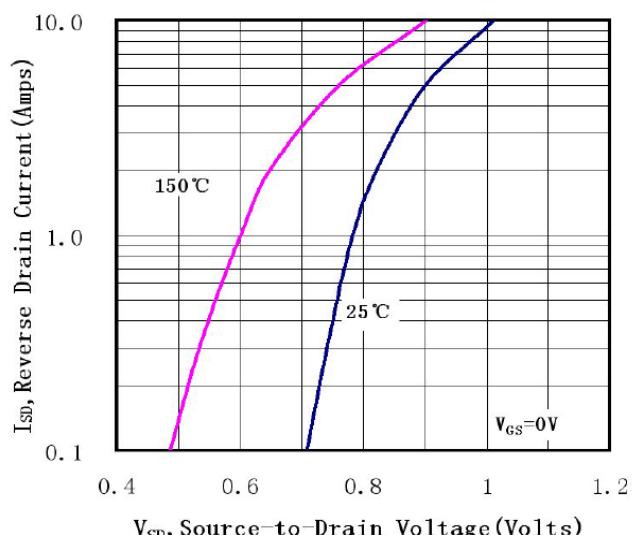


Fig5 Maximum Drain Current Vs.Case Temperature

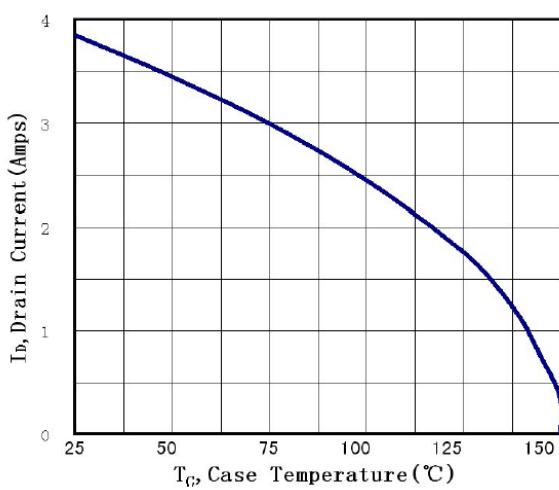
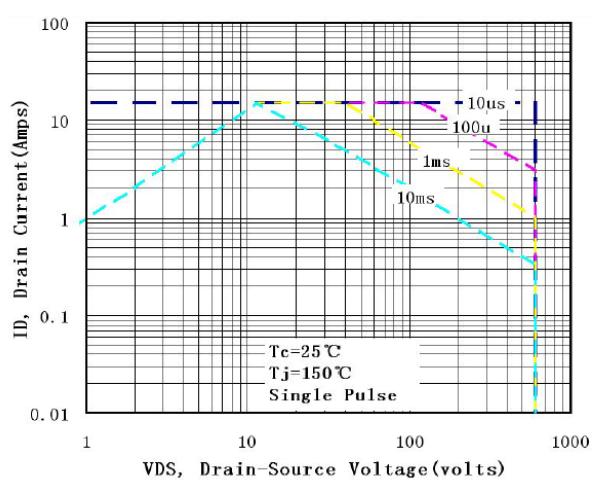


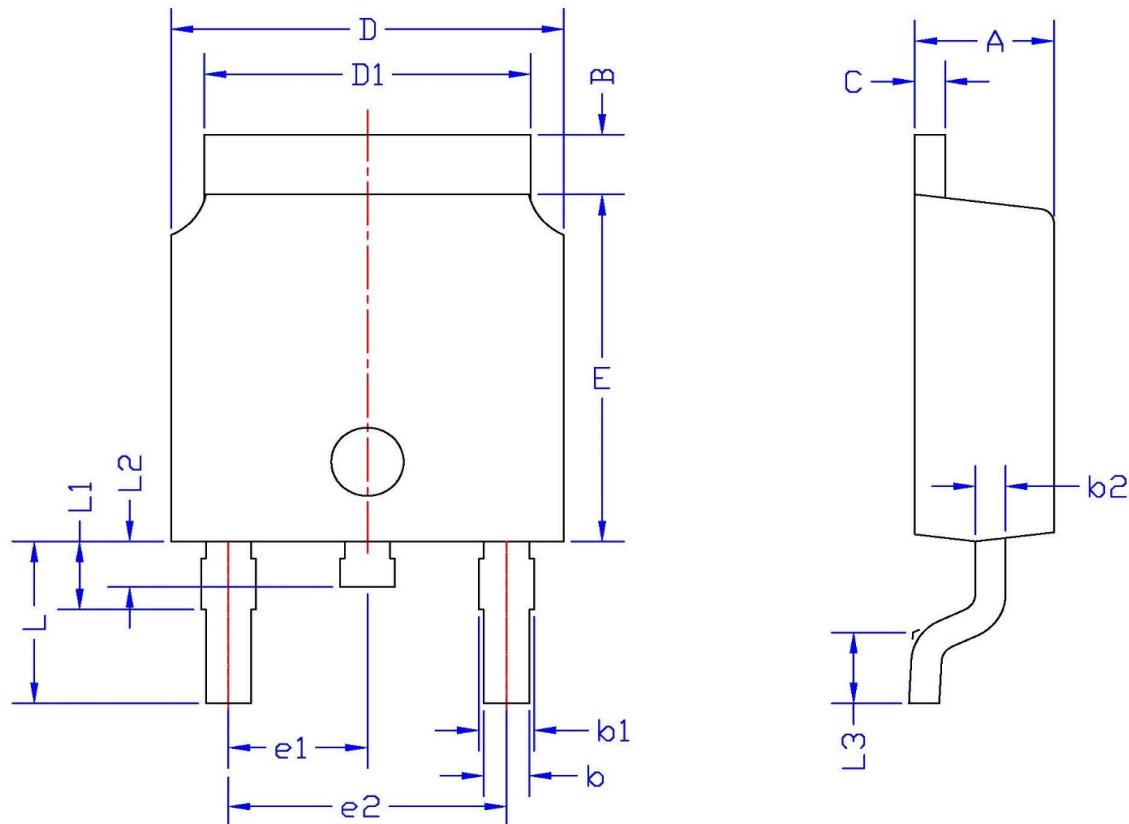
Fig6 Maximum Safe Operating Area



•Dimensions (TO-252)

UNIT:mm

SYMBOL	min	max	SYMBOL	min	max
A	2.10	2.50	L2	0.60	1.20
b	0.50	0.90	L3	1.20	1.80
b1	0.70	1.20	B	0.80	1.30
b2	0.40	0.70	C	0.40	0.70
D	6.20	6.80	D1	5.10	5.60
E	5.80	6.40	e1	2.10	2.45
L	3.60	4.60	e2	4.40	4.80
L1	0.80	1.60			



•Dimensions (TO-251)

UNIT:mm

SYMBOL	min	max	SYMBOL	min	max
A	2.10	2.50	B	0.80	1.30
b	0.50	0.90	C	0.40	0.70
b1	0.70	1.20	D1	5.10	5.60
b2	0.40	0.70	e1	2.10	2.45
D	6.20	6.80	e2	4.40	4.80
E	5.80	6.40			
L	3.60	9.80			
L1	0.80	1.60			

